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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	110592
Number of I/O	235
Number of Gates	600000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p600l-1fgg484i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Flash*Freeze Technology and Low Power Modes

Flash*Freeze Mode Device Behavior

Entering Flash*Freeze Mode

- IGLOO, IGLOO nano, IGLOO PLUS, ProASCI3L, and RT ProASIC3 devices are designed and optimized to enter Flash*Freeze mode only when power supplies are stable. If the device is being powered up while the FF pin is asserted (Flash*Freeze mode type 1), or while both FF pin and LSICC signal are asserted (Flash*Freeze mode type 2), the device is expected to enter Flash*Freeze mode within 5 µs after the I/Os and FPGA core have reached their activation levels.
- If the device is already powered up when the FF pin is asserted, the device will enter Flash*Freeze mode within 1 µs (type 1). In Flash*Freeze mode type 2 operation, entering Flash*Freeze mode is completed within 1 µs after both FF pin and LSICC signal are asserted. Exiting Flash*Freeze mode is completed within 1 µs after deasserting the FF pin only.

PLLs

- If an embedded PLL is used, entering Flash*Freeze mode will automatically power down the PLL.
- The PLL output clocks will stop toggling within 1 µs after the assertion of the FF pin in type 1, or after both FF pin and LSICC signal are asserted in type 2. At the same time, I/Os will transition into the state specified in Table 2-6 on page 29. The user design must ensure it is safe to enter Flash*Freeze mode.

I/Os and Globals

• While entering Flash*Freeze mode, inputs, globals, and PLLs will enter their Flash*Freeze state asynchronously to each other. As a result, clock and data glitches and narrow pulses may be generated while entering Flash*Freeze mode, as shown in Figure 2-5.

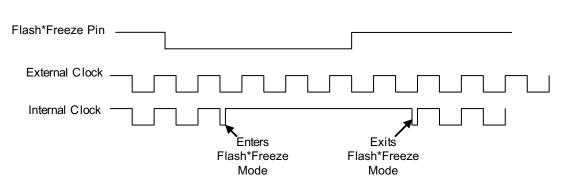


Figure 2-5 • Narrow Clock Pulses During Flash*Freeze Entrance and Exit

- I/O banks are not all deactivated simultaneously when entering Flash*Freeze mode. This can cause clocks and inputs to become disabled at different times, resulting in unexpected data being captured.
- Upon entering Flash*Freeze mode, all inputs and globals become tied High internally (except when an input hold state is used on IGLOO nano or IGLOO PLUS devices). If any of these signals are driven Low or tied Low externally, they will experience a Low to High transition internally when entering Flash*Freeze mode.
- Upon entering type 2 Flash*Freeze mode, ensure the LSICC signal (active High) does not deassert. This can prevent the device from entering Flash*Freeze mode.
- Asynchronous input to output paths may experience output glitches. For example, on a direct into-out path, if the current state is '0' and the input bank turns off first, the input and then the output will transition to '1' before the output enters its Flash*Freeze state. This can be prevented by using latches in asynchronous in-to-out paths.
- The above situations can cause glitches or invalid data to be clocked into and preserved in the device. Refer to the "Flash*Freeze Design Guide" section on page 34 for solutions.



Global Resources in Low Power Flash Devices

Using Spines of Occupied Global Networks

When a signal is assigned to a global network, the flash switches are programmed to set the MUX select lines (explained in the "Clock Aggregation Architecture" section on page 61) to drive the spines of that network with the global net. However, if the global net is restricted from reaching into the scope of a spine, the MUX drivers of that spine are available for other high-fanout or critical signals (Figure 3-20).

For example, if you want to limit the CLK1_c signal to the left half of the chip and want to use the right side of the same global network for CLK2_c, you can add the following PDC commands:

define_region -name region1 -type inclusive 0 0 34 29
assign_net_macros region1 CLK1_c
assign_local_clock -net CLK2_c -type chip B2

Figure 3-20 • Design Example Using Spines of Occupied Global Networks

Conclusion

IGLOO, Fusion, and ProASIC3 devices contain 18 global networks: 6 chip global networks and 12 quadrant global networks. These global networks can be segmented into local low-skew networks called spines. The spines provide low-skew networks for the high-fanout signals of a design. These allow you up to 252 different internal/external clocks in an A3PE3000 device. This document describes the architecture for the global network, plus guidelines and methodologies in assigning signals to globals and spines.

Related Documents

User's Guides

IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide http://www.microsemi.com/soc/documents/pa3_libguide_ug.pdf

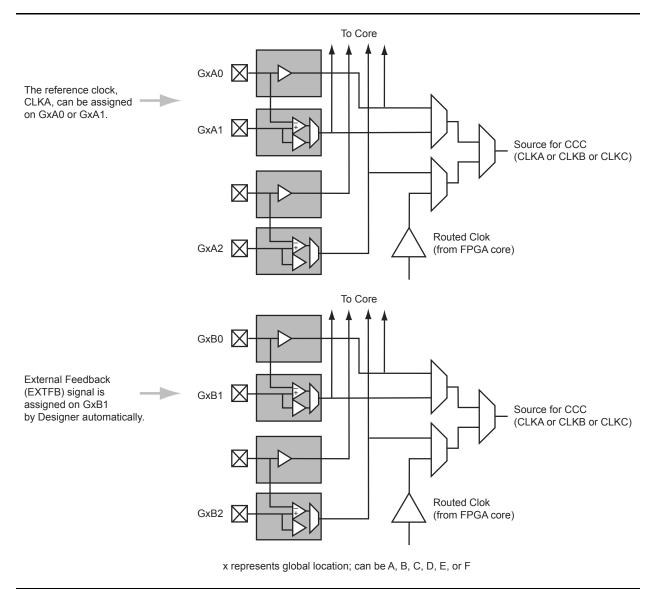


Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

Implementing EXTFB in ProASIC3/E Devices

When the external feedback (EXTFB) signal of the PLL in the ProASIC3/E devices is implemented, the phase detector of the PLL core receives the reference clock (CLKA) and EXTFB as inputs. EXTFB must be sourced as an INBUF macro and located at the global/chip clock location associated with the target PLL by Designer software. EXTFB cannot be sourced from the FPGA fabric.

The following example shows CLKA and EXTFB signals assigned to two global I/Os in the same global area of ProASIC3E device.





FlashROM in Microsemi's Low Power Flash Devices

FlashROM Support in Flash-Based Devices

The flash FPGAs listed in Table 5-1 support the FlashROM feature and the functions described in this document.

Table 5-1 • Flash-Based FPGAs

Series	Family [*]	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM [®] Cortex [™] -M1 soft processors, and flash memory into a monolithic device

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 5-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 5-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

FlashROM Generation and Instantiation in the Design

The SmartGen core generator, available in Libero SoC and Designer, is the only tool that can be used to generate the FlashROM content. SmartGen has several user-friendly features to help generate the FlashROM contents. Instead of selecting each byte and assigning values, you can create a region within a page, modify the region, and assign properties to that region. The FlashROM user interface, shown in Figure 5-10, includes the configuration grid, existing regions list, and properties field. The properties field specifies the region-specific information and defines the data used for that region. You can assign values to the following properties:

- Static Fixed Data—Enables you to fix the data so it cannot be changed during programming time. This option is useful when you have fixed data stored in this region, which is required for the operation of the design in the FPGA. Key storage is one example.
- 2. Static Modifiable Data—Select this option when the data in a particular region is expected to be static data (such as a version number, which remains the same for a long duration but could conceivably change in the future). This option enables you to avoid changing the value every time you enter new data.
- 3. Read from File—This provides the full flexibility of FlashROM usage to the customer. If you have a customized algorithm for generating the FlashROM data, you can specify this setting. You can then generate a text file with data for as many devices as you wish to program, and load that into the FlashPoint programming file generation software to get programming files that include all the data. SmartGen will optionally pass the location of the file where the data is stored if the file is specified in SmartGen. Each text file has only one type of data format (binary, decimal, hex, or ASCII text). The length of each data file must be shorter than or equal to the selected region length. If the data is shorter than the selected region length, the most significant bits will be padded with 0s. For multiple text files for multiple regions, the first lines are for the first device. In SmartGen, Load Sim. Value From File allows you to load the first device data in the MEM file for simulation.
- 4. Auto Increment/Decrement—This scenario is useful when you specify the contents of FlashROM for a large number of devices in a series. You can specify the step value for the serial number and a maximum value for inventory control. During programming file generation, the actual number of devices to be programmed is specified and a start value is fed to the software.

Figure 5-10 • SmartGen GUI of the FlashROM

recommended, since it reduces the complexity of the user interface block and the board-level JTAG driver.

Moreover, using an internal counter for address generation speeds up the initialization procedure, since the user only needs to import the data through the JTAG port.

The designer may use different methods to select among the multiple RAM blocks. Using counters along with demultiplexers is one approach to set the write enable signals. Basically, the number of RAM blocks needing initialization determines the most efficient approach. For example, if all the blocks are initialized with the same data, one enable signal is enough to activate the write procedure for all of them at the same time. Another alternative is to use different opcodes to initialize each memory block. For a small number of RAM blocks, using counters is an optimal choice. For example, a ring counter can be used to select from multiple RAM blocks. The clock driver of this counter needs to be controlled by the address generation process.

Once the addressing of one block is finished, a clock pulse is sent to the (ring) counter to select the next memory block.

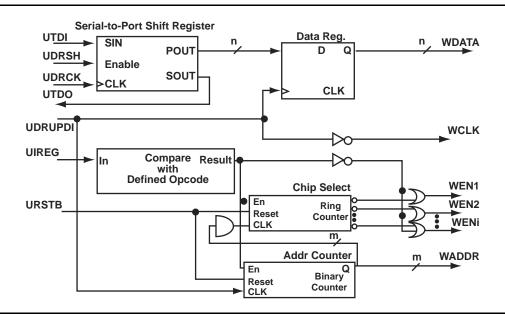


Figure 6-9 illustrates a simple block diagram of an interface block between UJTAG and RAM blocks.

Figure 6-9 • Block Diagram of a Sample User Interface

In the circuit shown in Figure 6-9, the shift register is enabled by the UDRSH output of the UJTAG macro. The counters and chip select outputs are controlled by the value of the TAP Instruction Register. The comparison block compares the UIREG value with the "start initialization" opcode value (defined by the user). If the result is true, the counters start to generate addresses and activate the WEN inputs of appropriate RAM blocks.

The UDRUPD output of the UJTAG macro, also shown in Figure 6-9, is used for generating the write clock (WCLK) and synchronizing the data register and address counter with WCLK. UDRUPD is HIGH when the TAP Controller is in the Data Register Update state, which is an indication of completing the loading of one data word. Once the TAP Controller goes into the Data Register Update state, the UDRUPD output of the UJTAG macro goes HIGH. Therefore, the pipeline register and the address counter place the proper data and address on the outputs of the interface block. Meanwhile, WCLK is defined as the inverted UDRUPD. This will provide enough time (equal to the UDRUPD HIGH time) for the data and address to be placed at the proper ports of the RAM block before the rising edge of WCLK. The inverter is not required if the RAM blocks are clocked at the falling edge of the write clock. An example of this is described in the "Example of RAM Initialization" section on page 166.

SRAM and FIFO Memories in Microsemi's Low Power Flash Devices

Date	Changes	Page			
v1.1 (continued)	Table 6-1 • Flash-Based FPGAs and associated text were updated to include the IGLOO PLUS family. The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.				
	The text introducing Table 6-8 • Memory Availability per IGLOO and ProASIC3 Device was updated to replace "A3P030 and AGL030" with "15 k and 30 k gate devices." Table 6-8 • Memory Availability per IGLOO and ProASIC3 Device was updated to remove AGL400 and AGLE1500 and include IGLOO PLUS and ProASIC3L devices.	162			



I/O Structures in IGLOO and ProASIC3 Devices

GTL+ (Gunning Transceiver Logic Plus)

This is an enhanced version of GTL that has defined slew rates and higher voltage levels. It requires a differential amplifier input buffer and an open-drain output buffer. Even though the output is open-drain, VCCI must be connected to either 2.5 V or 3.3 V. The reference voltage (VREF) is 1 V.

Differential Standards

These standards require two I/Os per signal (called a "signal pair"). Logic values are determined by the potential difference between the lines, not with respect to ground. This is why differential drivers and receivers have much better noise immunity than single-ended standards. The differential interface standards offer higher performance and lower power consumption than their single-ended counterparts. Two I/O pins are used for each data transfer channel. Both differential standards require resistor termination.

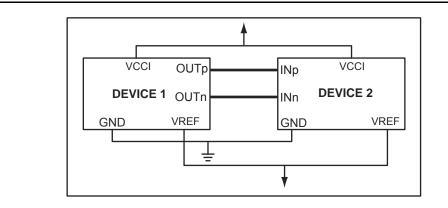


Figure 7-7 • Differential Topology

LVPECL (Low-Voltage Positive Emitter Coupled Logic)

LVPECL requires that one data bit be carried through two signal lines; therefore, two pins are needed per input or output. It also requires external resistor termination. The voltage swing between the two signal lines is approximately 850 mV. When the power supply is +3.3 V, it is commonly referred to as Low-Voltage PECL (LVPECL). Refer to the device datasheet for the full implementation of the LVPECL transmitter and receiver.

LVDS (Low-Voltage Differential Signal)

LVDS is a moderate-speed differential signaling system, in which the transmitter generates two different voltages that are compared at the receiver. LVDS uses a differential driver connected to a terminated receiver through a constant-impedance transmission line. It requires that one data bit be carried through two signal lines; therefore, the user will need two pins per input or output. It also requires external resistor termination. The voltage swing between the two signal lines is approximately 350 mV. VCCI is 2.5 V. Low power flash devices contain dedicated circuitry supporting a high-speed LVDS standard that has its own user specification. Refer to the device datasheet for the full implementation of the LVDS transmitter and receiver.

B-LVDS/M-LVDS

Bus LVDS (B-LVDS) refers to bus interface circuits based on LVDS technology. Multipoint LVDS (M-LVDS) specifications extend the LVDS standard to high-performance multipoint bus applications. Multidrop and multipoint bus configurations may contain any combination of drivers, receivers, and transceivers. Microsemi LVDS drivers provide the higher drive current required by B-LVDS and M-LVDS to accommodate the loading. The driver requires series terminations for better signal quality and to control voltage swing. Termination is also required at both ends of the bus, since the driver can be located anywhere on the bus. These configurations can be implemented using TRIBUF_LVDS and BIBUF_LVDS macros along with appropriate terminations. Multipoint designs using Microsemi LVDS macros can achieve up to 200 MHz with a maximum of 20 loads. A sample application is given in Figure 7-8. The input and output buffer delays are available in the LVDS sections in the datasheet.

I/O Structures in IGLOO and ProASIC3 Devices

Table 7-10 • Hot-Swap Level 3

Description	Hot-swap while bus idle
Power Applied to Device	Yes
Bus State	Held idle (no ongoing I/O processes during insertion/removal)
Card Ground Connection	Reset must be maintained for 1 ms before, during, and after insertion/removal.
Device Circuitry Connected to Bus Pins	Must remain glitch-free during power-up or power- down
Example Application	Board bus shared with card bus is "frozen," and there is no toggling activity on the bus. It is critical that the logic states set on the bus signal not be disturbed during card insertion/removal.
Compliance of IGLOO and ProASIC3 Devices	30K gate devices, all IGLOOe/ProASIC3E devices: Compliant with two levels of staging (first: GND; second: all other pins)
	Other IGLOO/ProASIC3 devices: Compliant:
	Option A – Two levels of staging (first: GND; second: all other pins) together with bus switch on the I/Os
	Option B – Three levels of staging (first: GND; second: supplies; third: all other pins)

Table 7-11 • Hot-Swap Level 4

Description	Hot-swap on an active bus
Description	
Power Applied to Device	Yes
Bus State	Bus may have active I/O processes ongoing, but device being inserted or removed must be idle.
Card Ground Connection	Reset must be maintained for 1 ms before, during, and after insertion/removal.
Device Circuitry Connected to Bus Pins	Must remain glitch-free during power-up or power- down
Example Application	There is activity on the system bus, and it is critical that the logic states set on the bus signal not be disturbed during card insertion/removal.
Compliance of IGLOO and ProASIC3 Devices	30K gate devices, all IGLOOe/ProASIC3E devices: Compliant with two levels of staging (first: GND; second: all other pins)
	Other IGLOO/ProASIC3 devices: Compliant:
	Option A – Two levels of staging (first: GND; second: all other pins) together with bus switch on the I/Os
	Option B – Three levels of staging (first: GND; second: supplies; third: all other pins)

	Clamp Diode ¹		Hot Insertion		5 V Input Tolerance ²		
I/O Assignment	AGL030 and A3P030	Other IGLOO and ProASIC3 Devices	AGL015 and AGL030	Other IGLOO Devices and All ProASIC3	AGL030 and A3P030	Other IGLOO and ProASIC3 Devices	Input and Output Buffer
3.3 V LVTTL/LVCMOS	No	Yes	Yes	No	Yes ²	Yes ²	Enabled/Disabled
3.3 V PCI, 3.3 V PCI-X	N/A	Yes	N/A	No	N/A	Yes ²	Enabled/Disabled
LVCMOS 2.5 V ⁵	No	Yes	Yes	No	Yes ²	Yes ⁴	Enabled/Disabled
LVCMOS 2.5 V/5.0 V ⁶	N/A	Yes	N/A	No	N/A	Yes ⁴	Enabled/Disabled
LVCMOS 1.8 V	No	Yes	Yes	No	No	No	Enabled/Disabled
LVCMOS 1.5 V	No	Yes	Yes	No	No	No	Enabled/Disabled
Differential, LVDS/ B-LVDS/M- LVDS/LVPECL	N/A	Yes	N/A	No	N/A	No	Enabled/Disabled

Table 7-12 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in IGLOO and ProASIC3 Devices

Notes:

1. The clamp diode is always off for the AGL030 and A3P030 device and always active for other IGLOO and ProASIC3 devices.

2. Can be implemented with an external IDT bus switch, resistor divider, or Zener with resistor.

3. Refer to Table 7-8 on page 189 to Table 7-11 on page 190 for device-compliant information.

4. Can be implemented with an external resistor and an internal clamp diode.

5. The LVCMOS 2.5 V I/O standard is supported by the 30 k gate devices only; select the LVCMOS25 macro.

6. The LVCMOS 2.5 V / 5.0 V I/O standard is supported by all IGLOO and ProASIC3 devices except 30K gate devices; select the LVCMOS5 macro.

Temporary overshoots are allowed according to the overshoot and undershoot table in the datasheet.

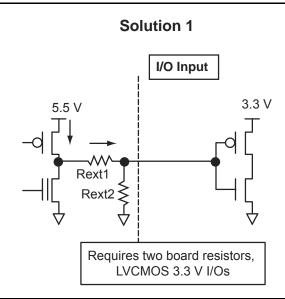
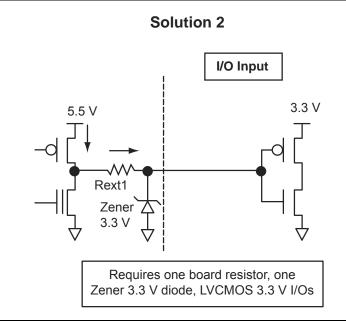


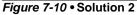
Figure 7-9 • Solution 1

Solution 2

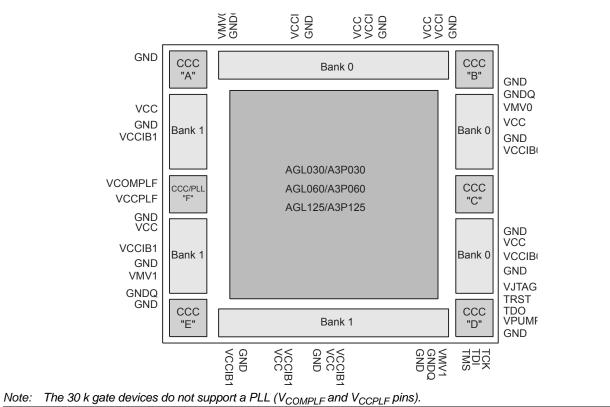
The board-level design must ensure that the reflected waveform at the pad does not exceed the voltage overshoot/undershoot limits provided in the datasheet. This is a requirement to ensure long-term reliability.

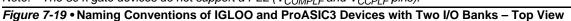
This scheme will also work for a 3.3 V PCI/PCI-X configuration, but the internal diode should not be used for clamping, and the voltage must be limited by the external resistors and Zener, as shown in Figure 7-10. Relying on the diode clamping would create an excessive pad DC voltage of 3.3 V + 0.7 V = 4 V.





ProASIC3L FPGA Fabric User's Guide





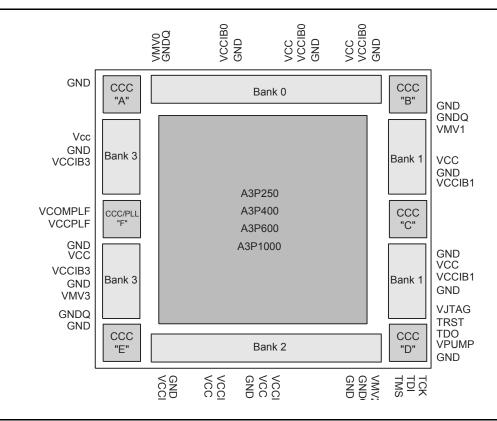


Figure 7-20 • Naming Conventions of IGLOO and ProASIC3 Devices with Four I/O Banks – Top View

Revision 4



I/O Structures in IGLOOe and ProASIC3E Devices

Features Supported on Every I/O

Table 8-6 lists all features supported by transmitter/receiver for single-ended and differential I/Os. Table 8-7 on page 219 lists the performance of each I/O technology.

Feature		Description
All I/O		High performance (Table 8-7 on page 219)
	•	Electrostatic discharge protection
	•	I/O register combining option
Single-Ended and Voltage-Referenced Transmitter Features	•	Hot-swap in every mode except PCI or 5 V–input– tolerant (these modes use clamp diodes and do not allow hot-swap)
	•	Activation of hot-insertion (disabling the clamp diode) is selectable by I/Os.
	•	Output slew rate: 2 slew rates
	•	Weak pull-up and pull-down resistors
	•	Output drive: 5 drive strengths
	•	Programmable output loading
	•	Skew between output buffer enable/disable time: 2 ns delay on rising edge and 0 ns delay on falling edge (see "Selectable Skew between Output Buffer Enable and Disable Times" section on page 236 for more information)
	•	LVTTL/LVCMOS 3.3 V outputs compatible with 5 V TTL inputs
Single-Ended Receiver Features	•	5 V-input-tolerant receiver (Table 8-13 on page 231)
	•	Schmitt trigger option
	•	Programmable delay: 0 ns if bypassed, 0.625 ns with '000' setting, 6.575 ns with '111' setting, 0.85-ns intermediate delay increments (at 25°C, 1.5 V)
	•	Separate ground plane for GNDQ pin and power plane for VMV pin are used for input buffer to reduce output-induced noise.
Voltage-Referenced Differential Receiver Features	•	Programmable delay: 0 ns if bypassed, 0.46 ns with '000' setting, 4.66 ns with '111' setting, 0.6-ns intermediate delay increments (at 25°C, 1.5 V)
	•	Separate ground plane for GNDQ pin and power plane for VMV pin are used for input buffer to reduce output-induced noise.
CMOS-Style LVDS, B-LVDS, M-LVDS, or LVPECL Transmitter	•	Two I/Os and external resistors are used to provide a CMOS-style LVDS, DDR LVDS, B-LVDS, and M-LVDS/LVPECL transmitter solution.
	•	Activation of hot-insertion (disabling the clamp diode) is selectable by I/Os.
	•	High slew rate
	•	Weak pull-up and pull-down resistors
	•	Programmable output loading
LVDS, DDR LVDS, B-LVDS, and M-LVDS/LVPECL Differential Receiver Features	•	Programmable delay: 0 ns if bypassed, 0.46 ns with '000' setting, 4.66 ns with '111' setting, 0.6-ns intermediate delay increments (at 25°C, 1.5 V)

I/O Structures in IGLOOe and ProASIC3E Devices

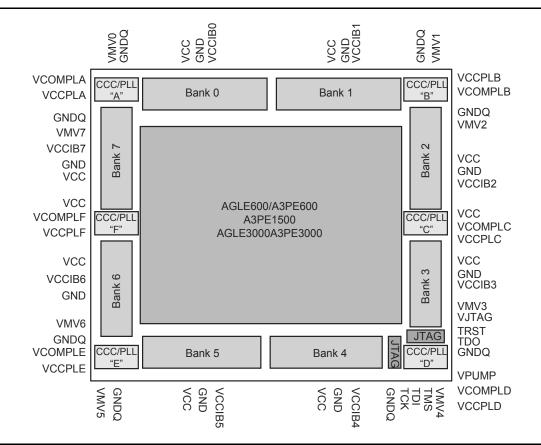


Figure 8-20 • User I/O Naming Conventions of IGLOOe and ProASIC3E Devices – Top View

Board-Level Considerations

Low power flash devices have robust I/O features that can help in reducing board-level components. The devices offer single-chip solutions, which makes the board layout simpler and more immune to signal integrity issues. Although, in many cases, these devices resolve board-level issues, special attention should always be given to overall signal integrity. This section covers important board-level considerations to facilitate optimum device performance.

Termination

Proper termination of all signals is essential for good signal quality. Nonterminated signals, especially clock signals, can cause malfunctioning of the device.

For general termination guidelines, refer to the *Board-Level Considerations* application note for Microsemi FPGAs. Also refer to the "Pin Descriptions" chapter of the appropriate datasheet for termination requirements for specific pins.

Low power flash I/Os are equipped with on-chip pull-up/-down resistors. The user can enable these resistors by instantiating them either in the top level of the design (refer to the *IGLOO, Fusion, and ProASIC3 Macro Library Guide* for the available I/O macros with pull-up/-down) or in the I/O Attribute Editor in Designer if generic input or output buffers are instantiated in the top level. Unused I/O pins are configured as inputs with pull-up resistors.

As mentioned earlier, low power flash devices have multiple programmable drive strengths, and the user can eliminate unwanted overshoot and undershoot by adjusting the drive strengths.

List of Changes

Date	Changes	Page				
August 2012	Figure 8-1 • DDR Configured I/O Block Logical Representation and Figure 8-3 • DDR Configured I/O Block Logical Representation were revised to indicate that resets on registers 1, 3, 4, and 5 are active high rather than active low. The title of the figures was revised from "I/O Block Logical Representation" (SAR 40685).					
	AGLE1500 was removed from Table 8-2 • Supported I/O Standards because it is not a valid offering. LVCMOS 1.2 was added to the single-ended standards. LVCMOS 1.2 was added to Table 8-3 • VCCI Voltages and Compatible IGLOOe and ProASIC3E Standards (SAR 33207).					
	Lack of a heading for the "User I/O Naming Convention" section made the information difficult to locate. A heading now introduces the user I/O naming conventions (SAR 38059).	245				
	Figure 8-5 • Simplified I/O Buffer Circuitry and Table 8-8 • Programmable I/O Features (user control via I/O Attribute Editor) were modified to indicate that programmable input delay control is applicable only to ProASIC3E, IGLOOe, ProASIC3EL, and RT ProASIC3 devices (SAR 39666).	222, 227				
	The hyperlink for the <i>Board-Level Considerations</i> application note was corrected (SAR 36663).	246, 248				
June 2011	Figure 8-1 • DDR Configured I/O Block Logical Representation and Figure 8-3 • DDR Configured I/O Block Logical Representation were revised so that the I/O_CLR and I/O_OCLK nets are no longer joined in front of Input Register 3 but instead on the branch of the CLR/PRE signal (SAR 26052).					
	The "Pro I/Os—IGLOOe, ProASIC3EL, and ProASIC3E" section was revised. Formerly it stated, "3.3 V PCI and 3.3 V PCI-X are 5 V–tolerant." This sentence now reads, "3.3 V PCI and 3.3 V PCI-X can be configured to be 5 V–tolerant" (SAR 20983).	215				
	Table 8-5 • Legal IGLOOe and ProASIC3E I/O Usage Matrix within the Same Bank was revised as follows (SAR 22467):	217				
	The combination of 3.3 V I/O bank voltage with 1.50 V minibank voltage and LVDS, B-LVDS, M-LVDS, and DDR was made an illegal combination (now gray instead of white).					
	The combination of 2.5 V I/O bank voltage with no minibank voltage and LVDS, B-LVDS, M-LVDS, and DDR was made a valid combination (now white instead of gray).					
	The following sentence was removed from the "LVCMOS (Low-Voltage CMOS)" section (SAR 22634): "All these versions use a 3.3 V-tolerant CMOS input buffer and a push-pull output buffer."	223				
	The "Electrostatic Discharge Protection" section was revised to remove references to tolerances (refer to the <i>Reliability Report</i> for tolerances). The Machine Model (MM) is not supported and was deleted from this section (SAR 24385).	231				
	The "I/O Interfacing" section was revised to state that low power flash devices are 5 V–input– and 5 V–output–tolerant if certain I/O standards are selected, removing "without adding any extra circuitry," which was incorrect (SAR 21404).	247				
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A				
v1.4 (December 2008)	The terminology in the "Low Power Flash Device I/O Support" section was revised.	214				

The following table lists critical changes that were made in each revision of the document.

I/O Software Control in Low Power Flash Devices

Output Buffers

There are two variations: Regular and Special.

If the **Regular** variation is selected, only the Width (1 to 128) needs to be entered. The default value for Width is 1.

The Special variation has Width, Technology, Output Drive, and Slew Rate options.

Bidirectional Buffers

There are two variations: Regular and Special.

The Regular variation has Enable Polarity (Active High, Active Low) in addition to the Width option.

The **Special** variation has Width, Technology, Output Drive, Slew Rate, and Resistor Pull-Up/-Down options.

Tristate Buffers

Same as Bidirectional Buffers.

DDR

There are eight variations: DDR with Regular Input Buffers, Special Input Buffers, Regular Output Buffers, Special Output Buffers, Regular Tristate Buffers, Special Tristate Buffers, Regular Bidirectional Buffers, and Special Bidirectional Buffers.

These variations resemble the options of the previous I/O macro. For example, the Special Input Buffers variation has Width, Technology, Voltage Level, and Resistor Pull-Up/-Down options. DDR is not available on IGLOO PLUS devices.

- 4. Once the desired configuration is selected, click the **Generate** button. The Generate Core window opens (Figure 9-4).
- 5. Enter a name for the macro. Click **OK**. The core will be generated and saved to the appropriate location within the project files (Figure 9-5 on page 257).

Figure 9-4 • Generate Core Window

6. Instantiate the I/O macro in the top-level code.

The user must instantiate the DDR_REG or DDR_OUT macro in the design. Use SmartGen to generate both these macros and then instantiate them in your top level. To combine the DDR macros with the I/O, the following rules must be met:

12 – Security in Low Power Flash Devices

Security in Programmable Logic

The need for security on FPGA programmable logic devices (PLDs) has never been greater than today. If the contents of the FPGA can be read by an external source, the intellectual property (IP) of the system is vulnerable to unauthorized copying. Fusion, IGLOO, and ProASIC3 devices contain state-of-the-art circuitry to make the flash-based devices secure during and after programming. Low power flash devices have a built-in 128-bit Advanced Encryption Standard (AES) decryption core (except for 30 k gate devices and smaller). The decryption core facilitates secure in-system programming (ISP) of the FPGA core array fabric, the FlashROM, and the Flash Memory Blocks (FBs) in Fusion devices. The FlashROM, Flash Blocks, and FPGA core fabric can be programmed independently of each other, allowing the FlashROM or Flash Blocks to be updated without the need for change to the FPGA core fabric.

Microsemi has incorporated the AES decryption core into the low power flash devices and has also included the Microsemi flash-based lock technology, FlashLock.[®] Together, they provide leading-edge security in a programmable logic device. Configuration data loaded into a device can be decrypted prior to being written to the FPGA core using the AES 128-bit block cipher standard. The AES encryption key is stored in on-chip, nonvolatile flash memory.

This document outlines the security features offered in low power flash devices, some applications and uses, as well as the different software settings for each application.

Figure 12-1 • Overview on Security



Security in Low Power Flash Devices

STAPL File with AES Encryption

- Does not contain AES key / FlashLock Key information
- · Intended for transmission through web or service to unsecured locations for programming

```
NOTE "CREATOR" "Designer Version: 6.1.1.108";
NOTE "DEVICE" "A3PE600";
NOTE "PACKAGE" "208 PQFP";
NOTE "DATE" "2005/04/08";
NOTE "DATE" "2005/04/08";
NOTE "STAPL_VERSION" "JESD71";
NOTE "IDCODE" "$123261CF";
NOTE "DESIGN" "counter32";
NOTE "DESIGN" "counter32";
NOTE "CHECKSUM" "$EF57";
NOTE "SAVE_DATA" "FROMStream";
NOTE "SAVE_DATA" "FROMStream";
NOTE "SECURITY" "ENCRYPT FROM CORE ";
NOTE "ALG_VERSION" "1";
NOTE "MAX_FREQ" "20000000";
NOTE "SILSIG" "$00000000";
```

Conclusion

The new and enhanced security features offered in Fusion, IGLOO, and ProASIC3 devices provide stateof-the-art security to designs programmed into these flash-based devices. Microsemi low power flash devices employ the encryption standard used by NIST and the U.S. government—AES using the 128-bit Rijndael algorithm.

The combination of an on-chip AES decryption engine and FlashLock technology provides the highest level of security against invasive attacks and design theft, implementing the most robust and secure ISP solution. These security features protect IP within the FPGA and protect the system from cloning, wholesale "black box" copying of a design, invasive attacks, and explicit IP or data theft.

Term	Explanation			
Security Header programming file	Programming file used to program the FlashLock Pass Key and/or AES key into the device to secure the FPGA, FlashROM, and/or FBs.			
AES (encryption) key	128-bit key defined by the user when the AES encryption option is set in the Microsemi Designer software when generating the programming file.			
FlashLock Pass Key	128-bit key defined by the user when the FlashLock option is set in the Microsemi Designer software when generating the programming file.			
	The FlashLock Key protects the security settings programmed to the device. Once a device is programmed with FlashLock, whatever settings were chosen at that time are secure.			
FlashLock	The combined security features that protect the device content from attacks. These features are the following:			
	Flash technology that does not require an external bitstream to program the device			
	 FlashLock Pass Key that secures device content by locking the security settings and preventing access to the device as defined by the user 			
	AES key that allows secure, encrypted device reprogrammability			

Glossary

References

National Institute of Standards and Technology. "ADVANCED ENCRYPTION STANDARD (AES) Questions and Answers." 28 January 2002 (10 January 2005).

See http://csrc.nist.gov/archive/aes/index1.html for more information.

UJTAG Applications in Microsemi's Low Power Flash Devices

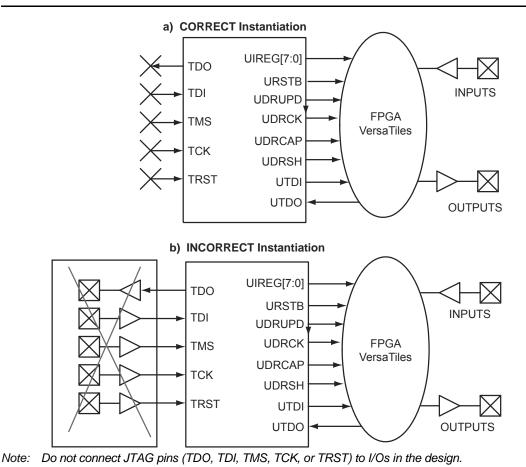


Figure 17-3 • Connectivity Method of UJTAG Macro

UJTAG Operation

There are a few basic functions of the UJTAG macro that users must understand before designing with it. The most important fundamental concept of the UJTAG design is its connection with the TAP Controller state machine.

TAP Controller State Machine

The 16 states of the TAP Controller state machine are shown in Figure 17-4 on page 367. The 1s and 0s, shown adjacent to the state transitions, represent the TMS values that must be present at the time of a rising TCK edge for a state transition to occur. In the states that include the letters "IR," the instruction register operates; in the states that contain the letters "DR," the test data register operates. The TAP Controller receives two control inputs, TMS and TCK, and generates control and clock signals for the rest of the test logic.

On power-up (or the assertion of TRST), the TAP Controller enters the Test-Logic-Reset state. To reset the controller from any other state, TMS must be held HIGH for at least five TCK cycles. After reset, the TAP state changes at the rising edge of TCK, based on the value of TMS.



Index

FlashLock IGLOO and ProASIC devices 307 permanent 307 FlashROM access using JTAG port 139 architecture 333 architecture of user nonvolatile 133 configuration 136 custom serialization 145 design flow 140 generation 141 programming and accessing 138 programming file 143 programming files 333 SmartGen 142 FlashROM read-back 371

G

global architecture 47 global buffers no programmable delays 80 with PLL function 83 with programmable delays 80 global macros Synplicity 66 globals designer flow 69 networks 74 spines and rows 57

Η

HLD code instantiating 258 hot-swapping 383

I

I/O banks standards 56 I/O standards 93 global macros 62 I/Os assigning technologies 264 assignments defined in PDC file 259 automatically assigning 268 behavior at power-up/-down 377 buffer schematic cell 257 cell architecture 273 configuration with SmartGen 254 global, naming 51 manually assigning technologies 264 software-controlled attributes 253 user I/O assignment flow chart 251 idle mode 23 INBUF_FF 39 ISP 289, 290 architecture 327 board-level considerations 337

circuit 343 microprocessor 349

J

JTAG 1532 327 JTAG interface 351

L

layout device-specific 94 LTC3025 linear voltage regulator 343

М

MAC validation/authentication 354 macros CLKBUF 93 CLKBUF_LVDS/LVPECL 93 CLKDLY 81, 89 FIFO4KX18 157 **PLL 89** PLL macro signal descriptions 84 RAM4K9 153 RAM512X18 155 supported basic RAM macros 152 UJTAG 365 **ULSICC 40** MCU FPGA programming model 352 memory availability 162 memory blocks 151 microprocessor programming 349 Microsemi SoC Products Group email 387 web-based technical support 387 website 387

0

OTP 289

Ρ

PDC global promotion and demotion 67 place-and-route 259 PLL behavior at brownout condition 381 configuration bits 106 core specifications 100 dynamic PLL configuration 103 functional description 101 power supply decoupling scheme 128 PLL block signals 84 PLL macro block diagram 85 power conservation 41 power modes Flash*Freeze 24 idle 23 shutdown 32